

# isc Thyristors

# BTA445Z-800BT

### **DESCRIPTION**

- With TO-3PN packaging
- Operating in 4 quadrants
- · High commutation capability
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

# TO-3PN package

### **APPLICATIONS**

- · Switching applications
- Phase control
- · Static switching on inductive or resistive load

# ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

| SYMBOL              | PARAMETER  | MAX        | UNIT |               |
|---------------------|--|------------|------|---------------|
| $V_{DRM}$           | Repetitive peak off-state voltage                                |            |      | V             |
| $V_{RRM}$           | Repetitive peak reverse voltage                                  |            |      | V             |
| I <sub>T(RSM)</sub> | Average on-state current Tc=105℃                                 | 45         | А    |               |
| I <sub>TSM</sub>    | Surge non-repetitive on-state current                            | 450<br>495 | А    |               |
| P <sub>G(AV)</sub>  | Average gate power dissipation ( over any 20 ms period ) Tj=125℃ |            |      | W             |
| Tj                  | Operating junction temperature                                   |            |      | ${\mathbb C}$ |
| $T_{stg}$           | Storage temperature  |            |      | $^{\circ}$    |



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### **ELECTRICAL CHARACTERISTICS (Tc=25℃ unless otherwise specified)**

| SYMBOL           | PARAMETER                         | CONDITIONS  |     |     | MIN | MAX | UNIT       |
|------------------|-----------------------------------|---|-----|-----|-----|-----|------------|
| I <sub>RRM</sub> | Repetitive peak reverse current   | V <sub>R</sub> =V <sub>RRM</sub> Rated; Tj=25℃<br>V <sub>D</sub> =V <sub>DRM</sub> Rated; Tj=125℃ |     |     |     | 10  | μ <b>Α</b> |
| I <sub>DRM</sub> | Repetitive peak off-state current |   |     |     |     | 2   | mA         |
| $V_{TM}$         | On-state voltage                  | I <sub>T</sub> =63.6A   |     |     |     | 1.7 | V          |
| I <sub>GT</sub>  | Gate-trigger current              |   |     | I   |     | 50  |            |
|                  |                                   | V <sub>D</sub> =12V;I <sub>T</sub> =0.1A  |     | II  |     | 50  | mA         |
|                  |                                   | VD = 12V,IT=0.1A  | III |     |     | 50  | -          |
|                  |                                   |   | IV  |     | 70  |     |            |
| $V_{GT}$         | Gate-trigger voltage              | V <sub>D</sub> =12V;I <sub>T</sub> =0.1A  |     | 1.3 | V   |     |            |
| Rth (j-c)        | Junction to case                  |   |     |     |     | 0.9 | °C/W       |

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